



ESDA14V2BP6

Application Specific Discretes
A.S.D.™

TRANSIL™

MAIN APPLICATIONS

Where transient overvoltage protection in ESD sensitive equipment is required, such as :

- Computers
- Printers
- Communication systems and cellular phones
- Video equipment

This device is particularly adapted to the protection of symmetrical signals.

FEATURES

- 4 Bidirectional Transil™ functions.
- ESD Protection: IEC61000-4-2 level 4
- Stand off voltage: 12V MIN
- Low leakage current < 1µA

DESCRIPTION

The ESDA14V2BP6 is a monolithic array designed to protect up to 4 lines in a bidirectional way against ESD transients.

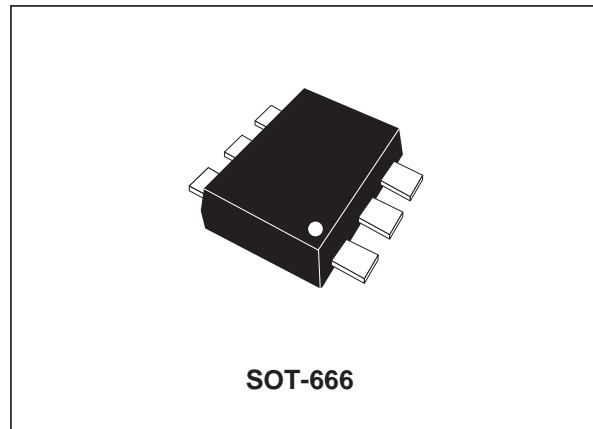
This device is ideal for applications where board space saving is required.

BENEFITS

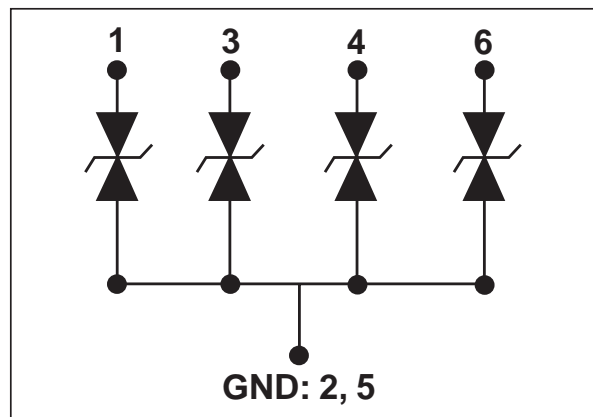
- High ESD protection level.
- High integration.
- Suitable for high density boards.

COMPLIES WITH THE FOLLOWING STANDARDS :

- **IEC61000-4-2 level 4:** 15 kV (air discharge)
8 kV (contact discharge)
- **MIL STD 883E-Method 3015-7:** class 3
25kV HBM (Human Body Model)



FUNCTIONAL DIAGRAM



ESDA14V2BP6

ABSOLUTE RATINGS (T_{amb} = 25°C)

Symbol	Parameter	Test conditions	Value	Unit
V _{PP}	ESD discharge - IEC61000-4-2 air discharge IEC61000-4-2 contact discharge		± 15 ± 8	kV
P _{PP}	Peak pulse power dissipation(8/20 μs). Note 1	T _j initial = T _{amb}	50	W
T _j	Junction temperature		125	°C
T _{stg}	Storage temperature range		- 55 to + 150	°C
T _L	Maximum lead temperature for soldering during 10s at 5mm for case		260	°C
T _{op}	Operating temperature range		- 40 to + 125	°C

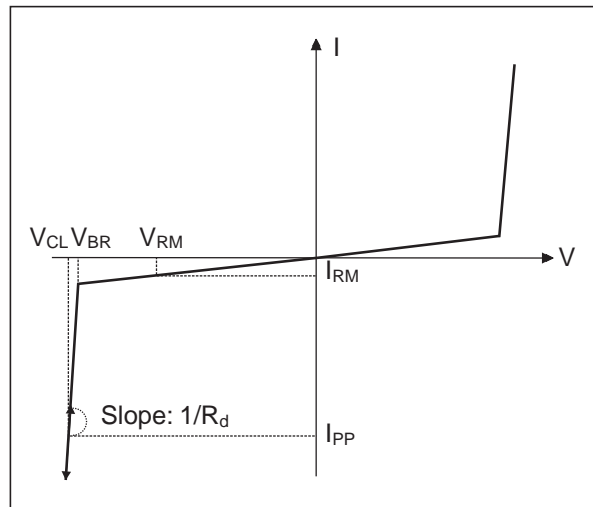
Note 1: for a surge greater than the maximum values, the diode will fail in short-circuit.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient on printed circuit on recommended pad layout	220	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter
V _{RM}	Stand-off voltage
V _{BR}	Breakdown voltage
V _{CL}	Clamping voltage
I _{RM}	Leakage current @ V _{RM}
I _{PP}	Peak pulse current
αT	Voltage temperature coefficient
V _F	Forward voltage drop



Types	I _{RM} @ V _{RM}		V _{BR} @ I _r		R _d typ.	αT typ.	C max.	
	max. μA	V	min. V	max. V				
ESDA14V2BP6	1	12	14.2	18	1	1.5	5.8	25
	0.1	3						

Fig. 1: Relative variation of peak pulse power versus initial junction temperature.

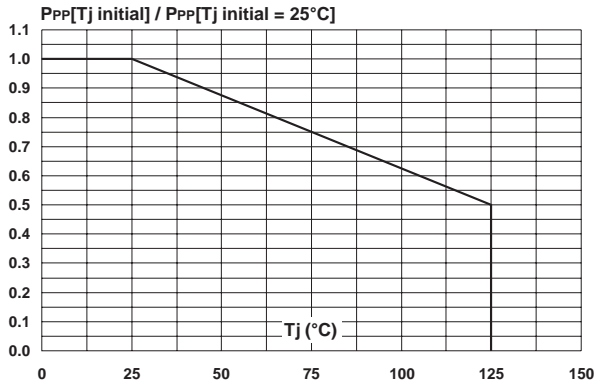


Fig. 2: Peak pulse power versus exponential pulse duration.

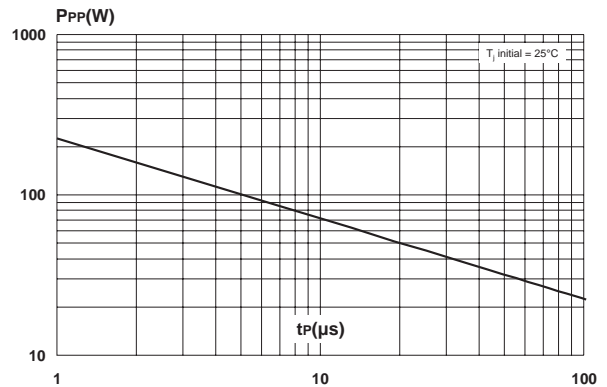


Fig. 3: Clamping voltage versus peak pulse current (typical values, rectangular waveform).

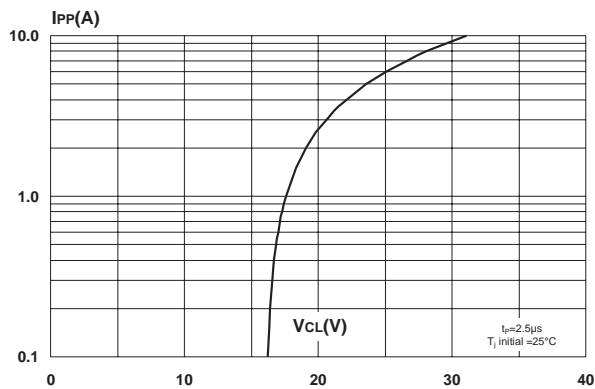


Fig. 4: Junction capacitance versus reverse voltage applied (typical values).

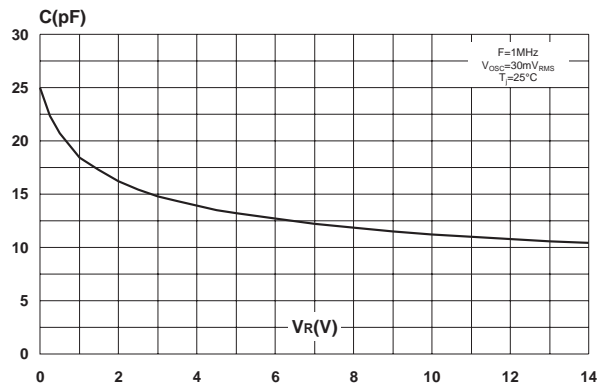
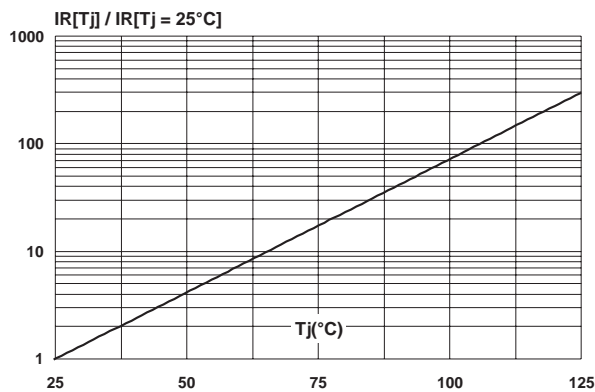
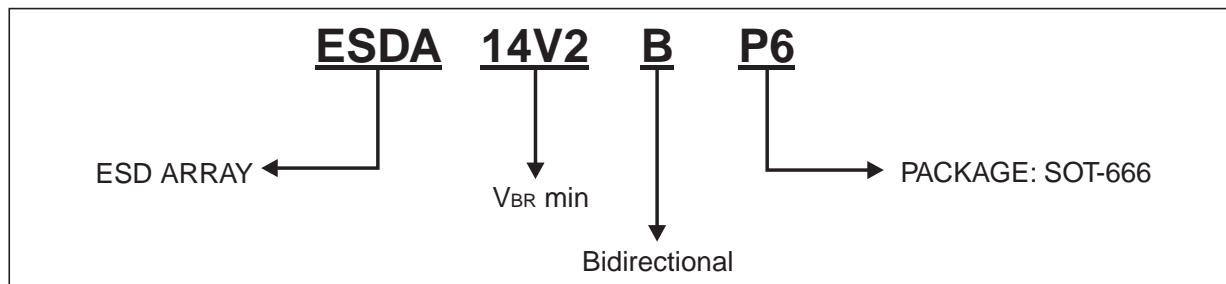


Fig. 5: Relative variation of leakage current versus junction temperature (typical values).

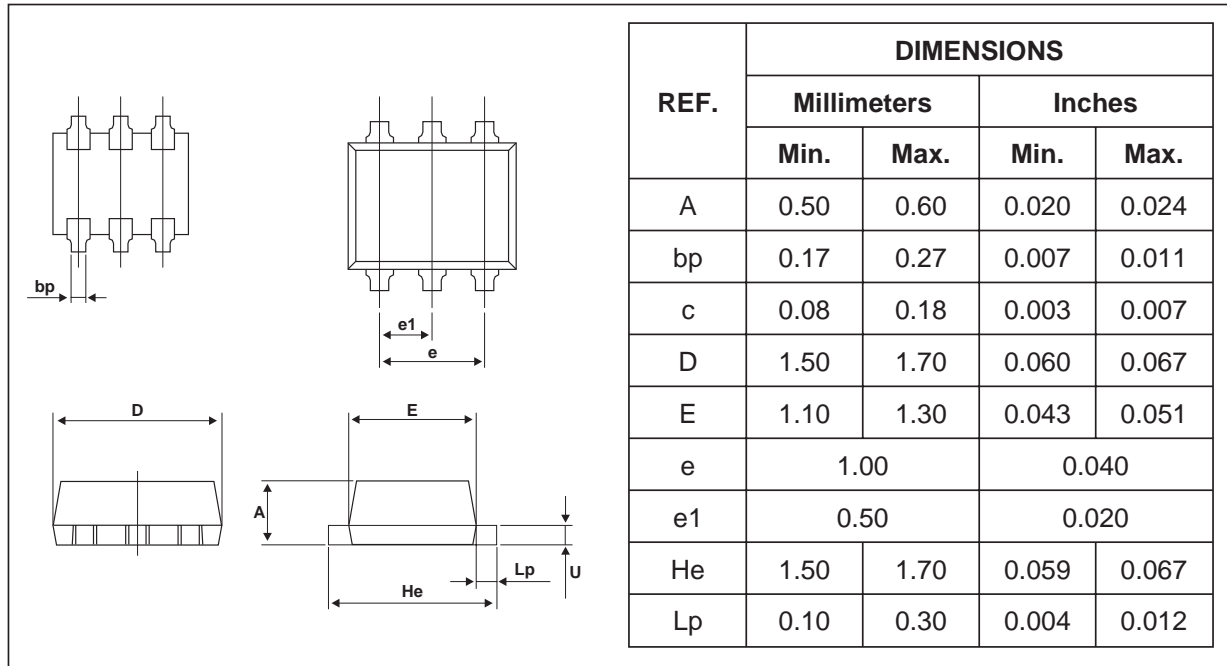
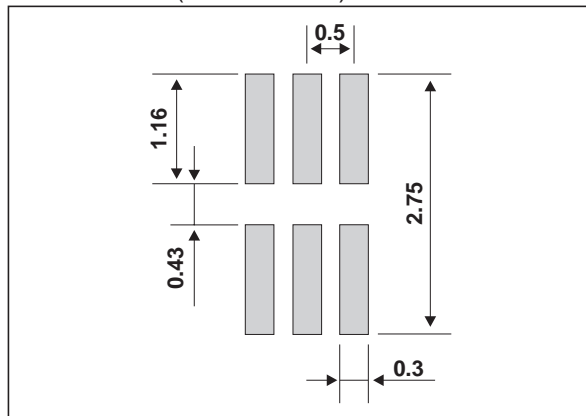


ESDA14V2BP6

ORDER CODE



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
ESDA14V2BP6	A	SOT-666	2.9 mg.	3000	Tape & reel 7"

PACKAGE MECHANICAL DATA
 SOT-666

FOOT PRINT (in millimeters)


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